

MT2301

Single P-Channel Power MOSFET

General Description

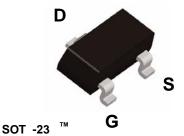
This P-Channel Power MOSFET is pro duced using MOS-TECH Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state r esistance and yet maintain low gate charge for superior switching performance.

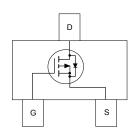
These devices are well suited for portable electronics applications: load s witching and power management, battery charging circuits and DC/DC conversion.



Features

- $-3.3 \text{ A}, -20 \text{ V}. R_{DS(ON)} = 0.072 \Omega \text{ @ } V_{GS} = -4.5 \text{ V}$ $R_{DS(ON)} = 0.096 \Omega \text{ @ } V_{GS} = -2.5 \text{ V}$
- Low gate charge (3.6 nC typical)
- High performance trench technology for extremely low R_{DS(ON)}
- SuperSOTTM -23 provides low R_{DS(ON)} and 30% higher power handling capability than SOT23 in the same footprint





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Drain Current - Continuous	(Note 1a)	-3.3	Α
	- Pulsed		–10	
P _D	Maximum Power Dissipation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T_J , T_{STG}	Operating and Storage Junction Tem	perature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
010X	MT2301	7"	8mm	3000 units	

Symbol	Parameter	Conditions	Mir	Тур	Max	Units
OFF CHAR	ACTERISTICS					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	I_D = -250 μ A, Referenced to 25 °C	С	-16		mV /°C
DSS	Zero Gate Voltage Drain Current	V _{DS} = -16 V, V _{GS} = 0 V			-1	μA
		$T_J =$	55°C		-10	μA
GSSF	Gate - Body Leakage, Forward	V _{GS} = 8 V, V _{DS} = 0 V			100	nA
GSSR	Gate - Body Leakage, Reverse	V _{GS} = -8 V, V _{DS} = 0 V			-100	nA
ON CHARA	CTERISTICS (Note 2)					
/ _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.8		-1.5	V
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold Voltage Temp. Coefficient	I_D = -250 μ A, Referenced to 25 °C	С	3		mV /°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -1.3 \text{ A}$		0.072	0.08	Ω
			125°C	0.12	0.15	
		$V_{GS} = -2.5 \text{ V}, I_D = -1.1 \text{ A}$		0.096	0.15	
D(ON)	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \ V_{DS} = -5 \text{ V}$	-3.	3		Α
FS	Forward Transconductance	$V_{DS} = -4.5 \text{ V}, I_{D} = -2 \text{ A}$		4		S
OYNAMIC C	HARACTERISTICS	<u>.</u>	•		•	•
oiss	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		330		pF
oss	Output Capacitance	f = 1.0 MHz		80		pF
Prss	Reverse Transfer Capacitance			35		pF
SWITCHING	CHARACTERISTICS (Note 2)					
D(on)	Turn - On Delay Time	$V_{DD} = -5 \text{ V}, I_{D} = -0.5 \text{ A},$		7	15	ns
	Turn - On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		12	22	ns
D(off)	Turn - Off Delay Time			16	26	ns
f	Turn - Off Fall Time			5	12	ns
Q_g	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -2 \text{ A},$ $V_{GS} = -4.5 \text{ V}$		3.6	5	nC
Q_{gs}	Gate-Source Charge	V _{GS} = -4.5 V		0.8		nC
\mathbf{Q}_{gd}	Gate-Drain Charge			0.7		nC
RAIN-SOU	RCE DIODE CHARACTERISTICS AND MAX	KIMUM RATINGS				
S	Maximum Continuous Drain-Source Diode Fo			-0.42	Α	
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -0.42 \text{ A} \text{ (Note)}$		-0.7	-1.2	V

Note:

^{1.} R_{aw} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the s older mounting surface of the drain pins. R_{ax} is guaranteed by design while R_{ax} is determined by the user's board design.



a. 250°C/W when mounted on a 0.02 in² pad of 2oz Cu.



b. 270°C/W when mounted on a 0.001 in² pad of 2oz Cu.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

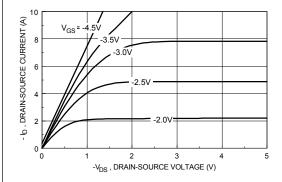


Figure 1. On-Region Characteristics.

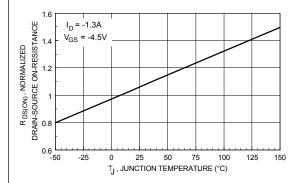


Figure 3. On-Resistance Variation with Temperature.

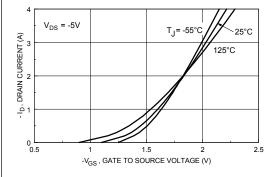


Figure 5. Transfer Characteristics.

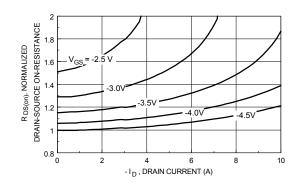


Figure 2. On-Resistance Variation with Drain Current and Gate

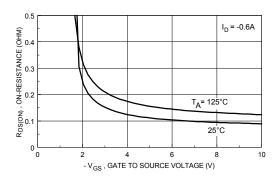


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

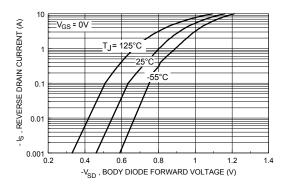


Figure 6. Body Diode Forward Voltage

Variation with Source

Current

and Temperature.

Typical Electrical Characteristics (continued)

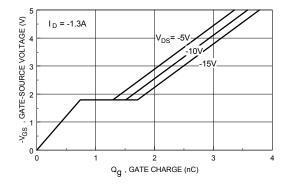


Figure 7. Gate Charge Characteristics.

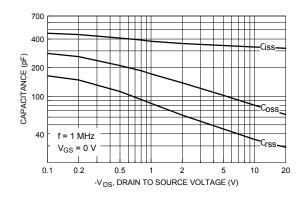


Figure 8. Capacitance Characteristics.

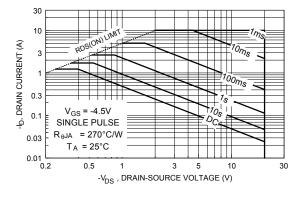


Figure 9. Maximum Safe Operating Area.

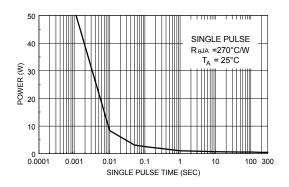


Figure 10. Single Pulse Maximum Power Dissipation.

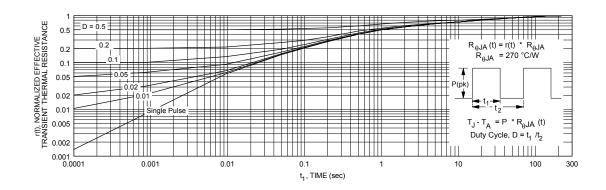
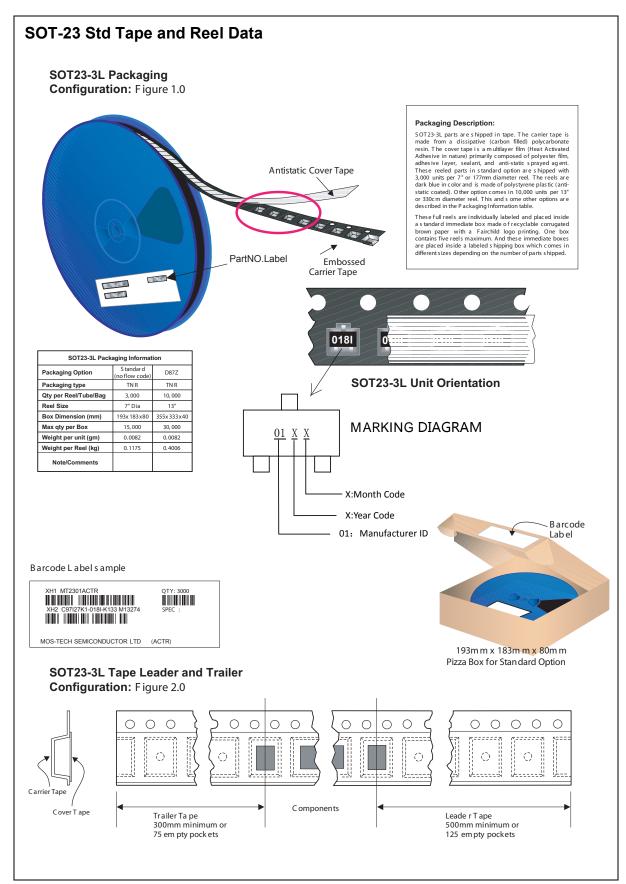


Figure 11. Transient Thermal Response Curve.

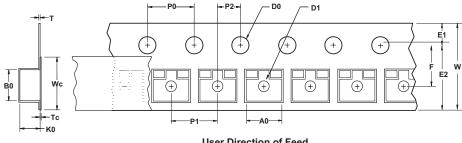
Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.



SOT-23 Std Tape and Reel Data, continued

SOT23-3L Embossed Carrier Tape

Configuration: Figure 3.0



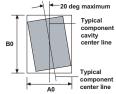
User Direction of Feed	

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

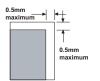
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

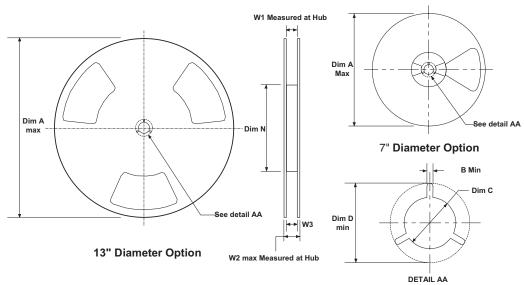


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

SOT23-3L Reel Configuration: Figure 4.0



Dimensions are in inches and millimeters											
Tape Size Reel Option Dim A Dim B Dim C Dim D Dim N Dim W1 Dim W2 Dim W3 (LS								Dim W3 (LSL-USL)			
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9		
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9		

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